



TSMC-02-276

April 9, 2004

To: Commissioner for Patents  
P.O.Box 1450  
Alexandria, VA 22313-1450

Fr: George O. Saile, Reg. No. 19,572  
28 Davis Avenue  
Poughkeepsie, N.Y. 12603

Subject: | Serial No. 10/798,063 03/11/04 |  
Howard Chih-Ho Wang et al.  
METHOD FOR FORMING DEVICES WITH  
MULTIPLE SPACER WIDTHS  
| \_\_\_\_\_ |

#### INFORMATION DISCLOSURE STATEMENT

Enclosed is Form PTO-1449, Information Disclosure Citation  
In An Application.

The following Patents and/or Publications are submitted to  
comply with the duty of disclosure under CFR 1.97-1.99 and  
37 CFR 1.56.

#### CERTIFICATE OF MAILING

I hereby certify that this correspondence is being  
deposited with the United States Postal Service as first class  
mail in an envelope addressed to: Commissioner for Patents,  
P.O. Box 1450, Alexandria, VA 22313-1450, on April 12, 2004.

Stephen B. Ackerman, Reg.# 37761

Signature/Date SBAR 4/12/04

U.S. Patent 6,344,398 to Hsu, "Method for Forming Transistor Devices with Different Spacer Width," discloses transistor devices on a wafer with different spacer widths.

U.S. Patent 5,874,330 to Ahn et al., "Method for Fabricating Semiconductor Device," describes a method of forming different sidewall thicknesses on gate electrodes in cell and peripheral circuitry regions.

U.S. Patent 6,248,623 to Chien et al., "Method for Manufacturing Embedded Memory with Different Spacer Widths," discusses embedded DRAM technology in which a three layer spacer consisting of a nitride layer between two oxide layers is formed.

U.S. Patent 6,316,304 to Pradeep et al., "Method of Forming Spacers of Multiple Widths," describes the formation of two different spacer widths on adjacent transistors.

Sincerely,

A handwritten signature in black ink, appearing to read 'S. B. Ackerman', written over a horizontal line.

Stephen B. Ackerman,  
Reg. No. 37761

Group 1st Unit

EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP § 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to the applicant.